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P.E.S. College of Engineering, Mandya - 571 401

(An Autonomous Institution affiliated to VTU, Belagavi)

Second Semester, M. Tech - VLSI Design and Embedded System (MECE)

Semester End Examination; June - 2017

Low Power VLSI Design

Time: 3 hrs

Max. Marks: 100

Note: Answer FIVE full questions, selecting ONE full question from each unit.

UNIT - I

- 1 a. Briefly discuss the static and dynamic power dissipation in CMOS circuits. 8
- b. Show that the short circuit power dissipation of an encoded inverter is 9
- $$P_{SC} = \frac{\beta}{12} (V_{DD} - V_T)^3 \frac{\tau}{T}.$$
- c. What is meant by overlap capacitance? Give its equation. 3
- 2 a. Discuss the impact of technology scaling and innovation trends for low power devices. 10
- b. What are the problems associated with transistor and gate sizing for dynamic power reduction? 4
- c. Explain the important components of diffusion capacitance with necessary equations. 6

UNIT - II

- 3 a. Discuss the following gate level logic simulation : 10
- i) Internal switching energy ii) Gate level capacitance estimation.
- b. Discuss the power models based on activities. 8
- c. What are the fundamental issues in composing a power model? 2
- 4 a. Bring out the differences between positive and negative correlation. 6
- b. Define Monte Carlo simulation process and also derive the expression for minimum number of samples 'N' by using Monte Carlo concept. 10
- c. The standard deviation of the power samples measured from a circuit has been observed to have $\pm 20\%$ fluctuations from the mean. How many samples are required to have 99% confidence that the error of sample mean is within $\pm 5\%$? Given $Z_{\alpha/2} = 2.58$. 4

UNIT - III

- 5 a. Derive the expression for average frequency 'F' of the circuit related to entropy of the signals. 10
- b. Compute the transition density and static probability of $y = ab+c$ given $p(a) = 0.2$, $p(b) = 0.3$, $p(c) = 0.4$, $D(a) = 1$, $D(b) = 2$ and $D(c) = 3$. 10

Contd....2

- 6 a. Briefly discuss the low power digital cell library. 8
- b. Explain the concept of glitches by considering CMOS XOR gate circuit. 6
- c. Discuss the low voltage swing circuit techniques. 6

UNIT - IV

- 7 a. Explain gate reorganization with necessary diagrams. 10
- b. Explain the architecture of bus invert encoding along with relevant diagrams. 10
- 8 a. Explain adaptive filtering with necessary diagrams. 10
- b. Discuss the concept of parallel architecture with voltage reduction. 10

UNIT - V

- 9 a. Explain how to insert buffer in clock tree with example. 10
- b. Derive the expression for tolerable skew. 10
- 10 a. Explain the algorithmic load analysis and optimization. 10
- b. Briefly discuss the architecture level estimation and synthesis. 10

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